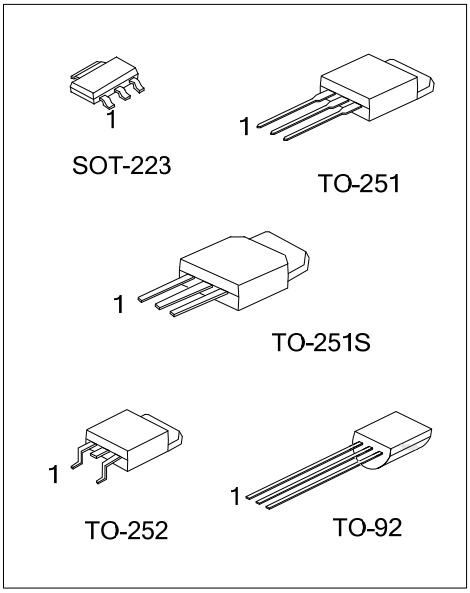
2A, 500V N-CHANNEL POWER MOSFET



■ DESCRIPTION

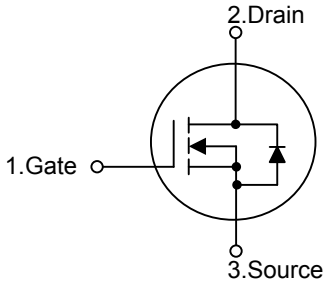
The UTC **2N50-CB** is an N-channel mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology allows a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **2N50-CB** is generally applied in high efficiency switch mode power supplies, active power factor correction and electronic lamp ballasts based on half bridge topology.

■ FEATURES

* $R_{DS(ON)}$ < 5.0Ω @ V_{GS}=10V, I_D=1.0A
* High switching speed
* 100% avalanche tested

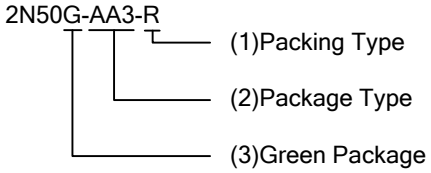
■ SYMBOL



■ ORDERING INFORMATION

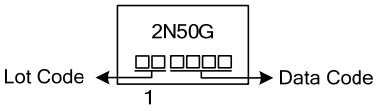
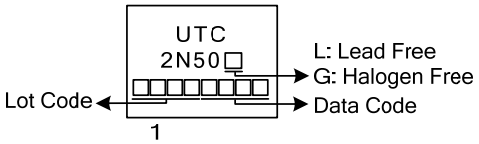
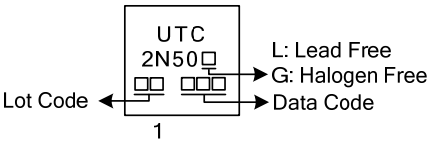
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
-	2N50G-AA3-R	SOT-223	G	D	S	Tape Reel
2N50L-TM3-T	2N50G-TM3-T	TO-251	G	D	S	Tube
2N50L-TMS-T	2N50G-TMS-T	TO-251S	G	D	S	Tube
2N50L-TN3-R	2N50G-TN3-R	TO-252	G	D	S	Tape Reel
2N50L-T92-B	2N50G-T92-B	TO-92	G	D	S	Tape Box
2N50L-T92-K	2N50G-T92-K	TO-92	G	D	S	Bulk

Note: Pin Assignment: G: Gate D: Drain S: Source



(1) B: Tape Box, K: Bulk, T: Tube, R: Tape Reel
(2) AA3: SOT-223, TM3: TO-251, TMS: TO-251S
TN3: TO-252, T92: TO-92
(3) L: Lead Free, G: Halogen Free and Lead Free

■ MARKING

PACKAGE	MARKING
SOT-223	
TO-251 / TO-251S / TO-252	
TO-92	

■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	500	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous	I_D	2.0	A
	Pulsed (Note 2)	I_{DM}	8.0	A
Avalanche Current (Note 2)		I_{AR}	1.4	A
Avalanche Energy	Single Pulsed	E_{AS}	10	mJ
Power Dissipation	SOT-223	P_D	8.9	W
	TO-251/TO-251S TO-252		50	W
	TO-92		1.42	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. Drain current limited by maximum junction temperature.
4. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
5. L=10mH, I_{AS}=1.4A, V_{DD}=50V, R_G=25 Ω, Starting T_J = 25°C.
6. I_{SD}≤2.0A, di/dt≤200A/μs, V_{DD}≤BV_{DSS}, Starting T_J=25°C.

■ THERMAL DATA

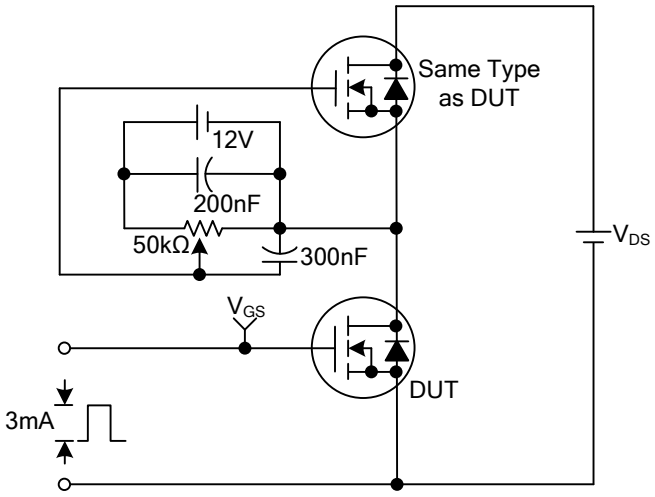
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	SOT-223	θ_{JA}	150	°C/W
	TO-251/TO-251S TO-252		110	°C/W
	TO-92		160	°C/W
Junction to Case	SOT-223	θ_{JC}	14	°C/W
	TO-251/TO-251S TO-252		2.5	°C/W
	TO-92		88	°C/W

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise noted)

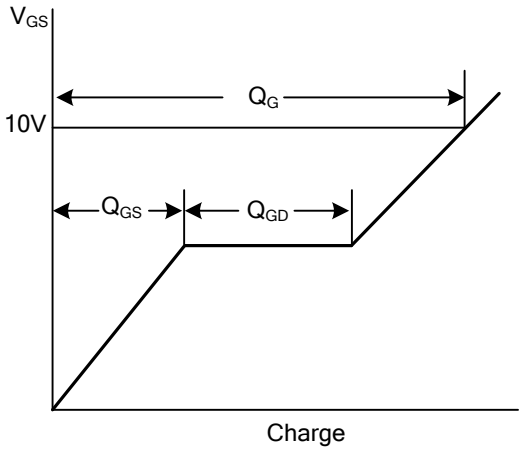
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=250μA, V_{GS}=0V	500			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=500V, V_{GS}=0V			1	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS}=+30V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-30V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=1A			5.0	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		153		pF
Output Capacitance		C_{OSS}			25.3		pF
Reverse Transfer Capacitance		C_{RSS}			4.7		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V_{DS}=50V, V_{GS}=10V, I_D=1.3A, I_G=250μA (Note 1, 2)		12.6		nC
Gate to Source Charge		Q_{GS}			1.3		nC
Gate to Drain Charge		Q_{GD}			0.8		nC
Turn-ON Delay Time		$t_{D(ON)}$	V_{DD} =30V, V_{GS}=10V, I_D =0.5A, R_G=25Ω (Note 1, 2)		26		ns
Rise Time		t_R			18		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			62		ns
Fall-Time		t_F			25		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				2	A
Maximum Body-Diode Pulsed Current		I_{SM}				8	A
Drain-Source Diode Forward Voltage		V_{SD}	I_S=2A, V_{GS}=0V			1.4	V
Reverse Recovery Time		t_{rr}	V_{GS}=0V, I_S = 2A, di/dt = 100A/μs		140		ns
Reverse Recovery Charge		Q_{rr}			0.48		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%
2. Essentially independent of operating temperature

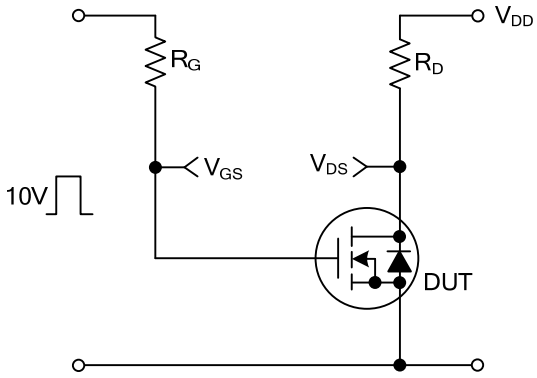
■ TEST CIRCUITS AND WAVEFORMS



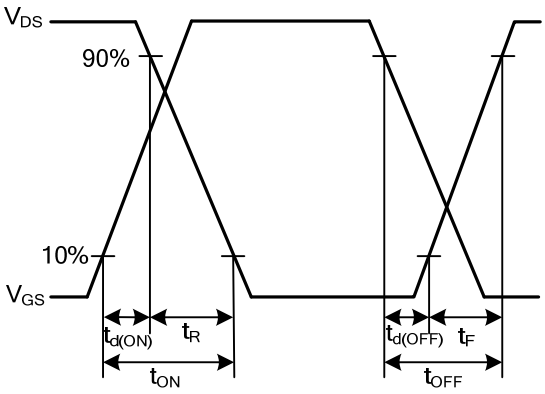
Gate Charge Test Circuit



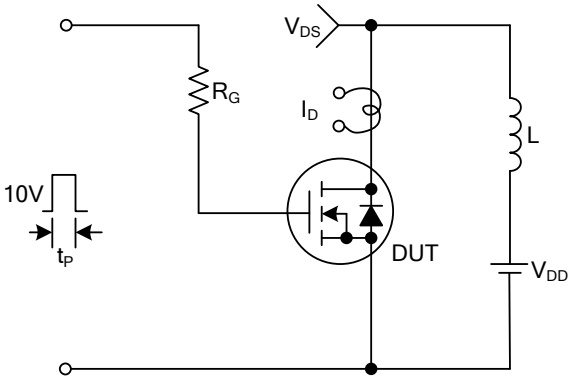
Gate Charge Waveforms



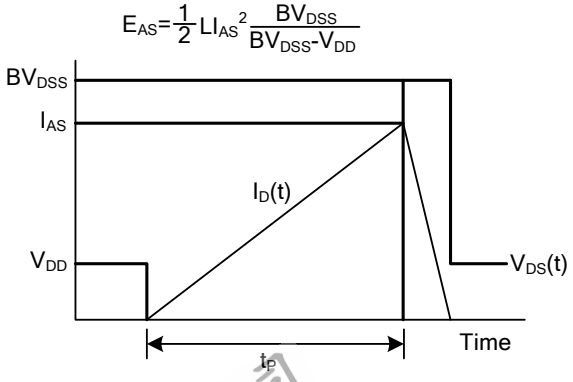
Resistive Switching Test Circuit



Resistive Switching Waveforms

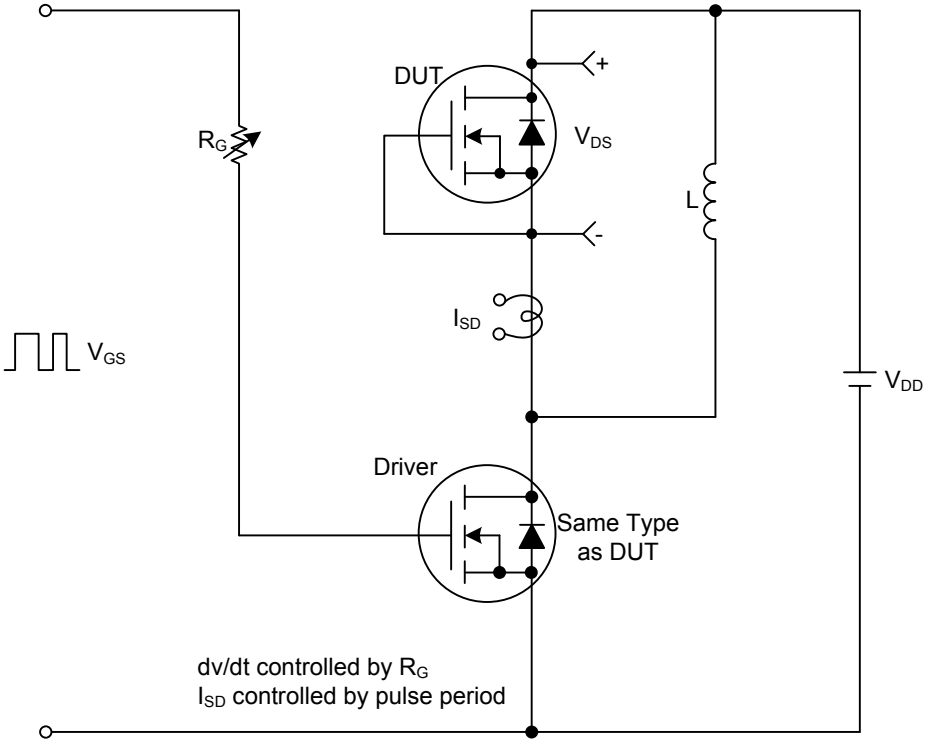


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TEST CIRCUITS AND WAVEFORMS(Cont.)



Peak Diode Recovery dv/dt Test Circuit & Waveforms